



Docket No. 8733.132.20 (LAN423)

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In Re application of:

Joon-Young YANG

Group Art Unit: 2814

Serial No.: 09/875,197

Examiner: UNKNOWN

Filed: June 7, 2001

For: METHOD OF FABRICATING A THIN FILM TRANSISTOR

PRELIMINARY AMENDMENT

Commissioner of Patents  
Washington, D.C. 20231

Sir:

Prior to issuance of a first Office Action, please amend the above-referenced application as follows:

IN THE CLAIMS:

Please **ADD** new Claims 21-40 as follows:

21. A method of fabricating a thin film transistor, comprising the steps of:
- depositing a gate insulating material and a gate metal layer on an active layer;
- forming a gate, a gate insulating layer, and an exposed portion of the active layer by etching the gate metal layer and by etching the gate insulating material;
- temporarily exciting a region of the active layer by implanting hydrogen ions into the exposed portion of the active layer while using the gate as a mask; and
- forming an impurity region by implanting self-activating impurity ions into the temporarily excited region while that region is excited.
22. The method of claim 21, wherein the gate insulating layer is formed by depositing silicon dioxide or silicon nitride on a glass substrate.

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